



# JCS2N60

## 主要参数 MAIN CHARACTERISTICS

$I_D$	2.0 A
$V_{DS}$	600 V
$R_{dson-max}$ ( $V_{gs}=10V$ )	5 $\Omega$
$Q_g$	15.3 nC

### 用途

- 高频开关电源
- 电子镇流器
- UPS 电源

### APPLICATIONS

- High frequency switching mode power supply
- Electronic ballast
- UPS

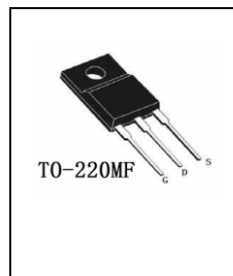
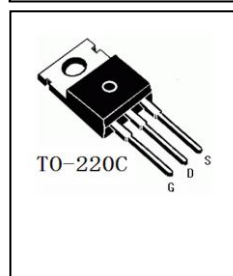
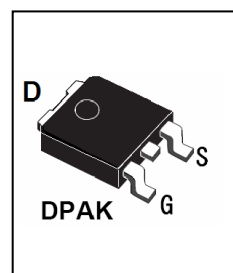
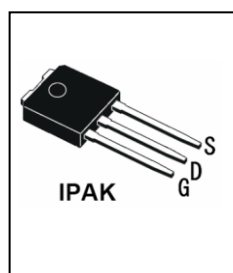
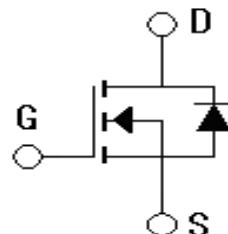
### 产品特性

- 低栅极电荷
- 低  $C_{rss}$  (典型值 7.6pF)
- 开关速度快
- 产品全部经过雪崩测试
- 高抗  $dv/dt$  能力
- RoHS 产品

### FEATURES

- Low gate charge
- Low  $C_{rss}$  (typical 7.6pF)
- Fast switching
- 100% avalanche tested
- Improved  $dv/dt$  capability
- RoHS product

## 封装 Package



## 订货信息 ORDER MESSAGE

订货型号 Order codes				印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen-Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen-Free-Reel		
JCS2N60R -R-B	JCS2N60R -R-BR	JCS2N60R-R-A	JCS2N60R-R-AR	JCS2N60R	DPAK
JCS2N60V -V-B	JCS2N60V -V-BR	N/A	N/A	JCS2N60V	IPAK
JCS2N60C -C-B	JCS2N60C -C -BR	N/A	N/A	JCS2N60C	TO-220C
JCS2N60F -F-B	JCS2N60F -F -BR	N/A	N/A	JCS2N60F	TO-220MF





## 绝对最大额定值 ABSOLUTE RATINGS (Tc=25℃)

项 目 Parameter	符 号 Symbol	数 值 Value			单 位 Unit
		JCS2N60V/R	JCS2N60C	JCS2N60F	
最高漏极-源极直流电压 Drain-Source Voltage	V <sub>DSS</sub>	600			V
连续漏极电流 Drain Current-continuous	I <sub>D</sub> T=25℃ T=100℃	1.9	2.0	2.0*	A
		1.1	1.3	1.3*	A
最大脉冲漏极电流(注1) Drain Current – pulse (note 1)	I <sub>DM</sub>	6.0			A
最高栅源电压 Gate-Source Voltage	V <sub>GSS</sub>	±30			V
单脉冲雪崩能量(注2) Single Pulsed Avalanche Energy (note 2)	E <sub>AS</sub>	120			mJ
雪崩电流(注1) Avalanche Current(note 1)	I <sub>AR</sub>	2.0			A
重复雪崩能量(注1) Repetitive Avalanche Energy (note 1)	E <sub>AR</sub>	5.4			mJ
二极管反向恢复最大电 压变化速率(注3) Peak Diode Recovery Dv/dt (note 3)	dv/dt	5.5			V/ns
耗散功率 Power Dissipation	P <sub>D</sub> T <sub>C</sub> =25℃ -Derate above 25℃	44	54	23	W
		0.35	0.43	0.18	W/℃
最高结温及存储温度 Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55~+150			℃
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T <sub>L</sub>	300			℃

\*漏极电流由最高结温限制

\*Drain current limited by maximum junction temperature





## 电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最大 Min	典型 Typ	最大 Max	单 位 Units
<b>关态特性 Off –Characteristics</b>						
漏—源击穿电压 Drain-Source Voltage	$BV_{DSS}$	$I_D=250\mu A, V_{GS}=0V$	600	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=1mA$ , referenced to $25^\circ C$	-	0.65	-	$V/^\circ C$
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=600V, V_{GS}=0V,$ $T_C=25^\circ C$	-	-	10	$\mu A$
		$V_{DS}=480V, T_C=125^\circ C$	-	-	100	$\mu A$
正向栅极体漏电流 Gate-body leakage current, forward	$I_{GSSF}$	$V_{DS}=0V, V_{GS}=30V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	$I_{GSSR}$	$V_{DS}=0V, V_{GS}=-30V$	-	-	-100	nA
<b>通态特性 On-Characteristics</b>						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	2.0	-	4.0	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=1A$	-	3.8	5.0	$\Omega$
正向跨导 Forward Transconductance	$g_{fs}$	$V_{DS}=40V, I_D=1.0A$ (note 4)	-	2.05	-	S
<b>动态特性 Dynamic Characteristics</b>						
栅极电阻 Gate resistance	$R_g$	$F=1.0MHz$ open drain	0.8	-	4.5	$\Omega$
输入电容 Input capacitance	$C_{iss}$	$V_{DS}=25V,$ $V_{GS}=0V,$ $f=1.0MHz$	180	380	490	pF
输出电容 Output capacitance	$C_{oss}$		16	35	46	pF
反向传输电容 Reverse transfer capacitance	$C_{rss}$		3.0	7.6	9.9	pF





## 电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics						
延迟时间 Turn-On delay time	$t_{d(on)}$	$V_{DD}=300V, I_D=2.0A, R_G=25\Omega$ (note 4, 5)	-	16	40	ns
上升时间 Turn-On rise time	$t_r$		-	50	110	ns
延迟时间 Turn-Off delay time	$t_{d(off)}$		-	40	90	ns
下降时间 Turn-Off Fall time	$t_f$		-	40	90	ns
栅极电荷总量 Total Gate Charge	$Q_g$	$V_{DS}=480V,$ $I_D=2.0A$ $V_{GS}=10V$ (note 4, 5)	-	15.3	19	nC
栅-源电荷 Gate-Source charge	$Q_{gs}$		-	1.8	5.0	nC
栅-漏电荷 Gate-Drain charge	$Q_{gd}$		-	7.2	16.0	nC
漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current		$I_S$	-	-	2.0	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current		$I_{SM}$	-	-	6.0	A
正向压降 Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V,$ $I_S=2.0A$	-	-	1.4	V
反向恢复时间 Reverse recovery time	$t_{rr}$	$V_{GS}=0V, I_S=2.0A$ $dI_F/dt=100A/\mu s$ (note 4)	-	250	600	ns
反向恢复电荷 Reverse recovery charge	$Q_{rr-}$		-	1.31	4.0	$\mu C$

## 热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	最大 Max			单 位 Unit
		JCS2N60V/ R	JCS2N60C	JCS2N60F	
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	2.87	2.32	5.50	$^{\circ}C/W$
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	110	62.5	62.5	$^{\circ}C/W$

注释:

- 1: 脉冲宽度由最高结温限制
- 2:  $L=55mH, I_{AS}=2.0A, V_{DD}=50V, R_G=25\Omega$ , 起始结温  $T_J=25^{\circ}C$
- 3:  $I_{SD} \leq 2A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$ , 起始结温  $T_J=25^{\circ}C$
- 4: 脉冲测试: 脉冲宽度  $\leq 300\mu s$ , 占空比  $\leq 2\%$
- 5: 基本与工作温度无关

Notes:

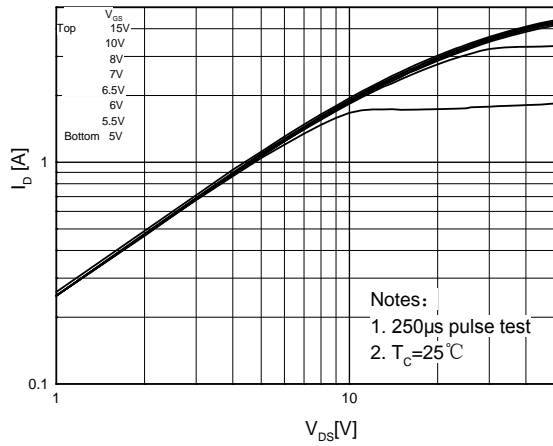
- 1: Pulse width limited by maximum junction temperature
- 2:  $L=55mH, I_{AS}=2.0A, V_{DD}=50V, R_G=25\Omega$ , Starting  $T_J=25^{\circ}C$
- 3:  $I_{SD} \leq 2A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$ , Starting  $T_J=25^{\circ}C$
- 4: Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycles  $\leq 2\%$



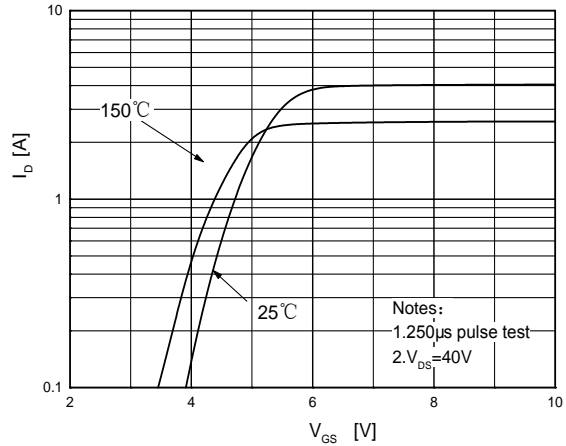


# 特征曲线 ELECTRICAL CHARACTERISTICS (curves)

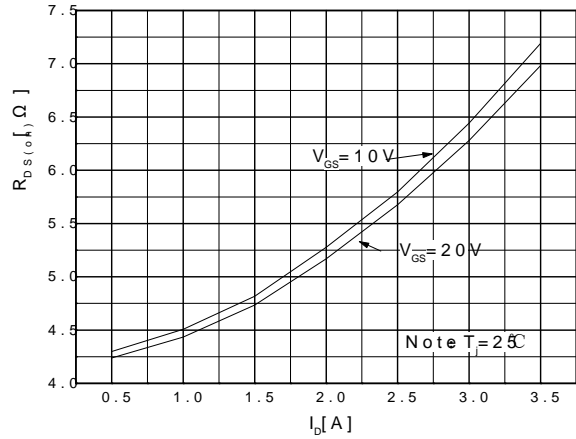
## On-Region Characteristics



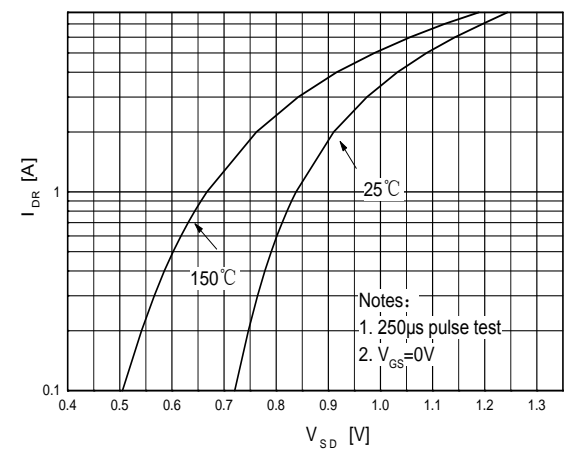
## Transfer Characteristics



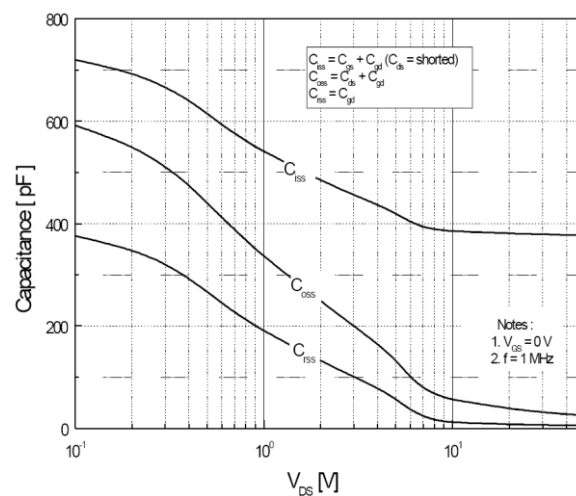
## On-Resistance Variation vs. Drain Current and Gate Voltage



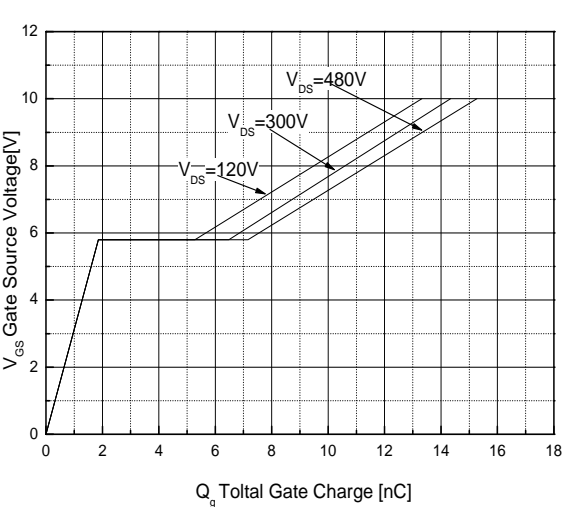
## Body Diode Forward Voltage Variation vs. Source Current and Temperature



## Capacitance Characteristics



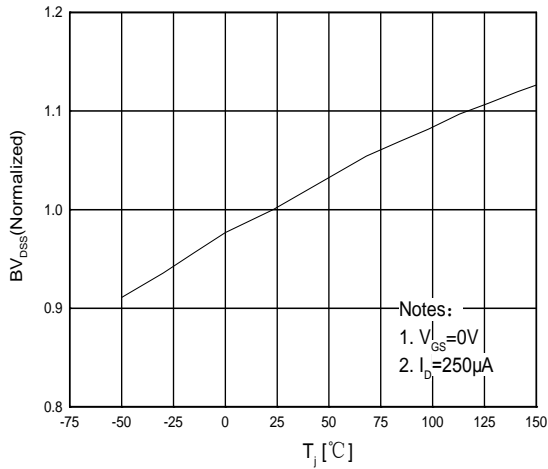
## Gate Charge Characteristics



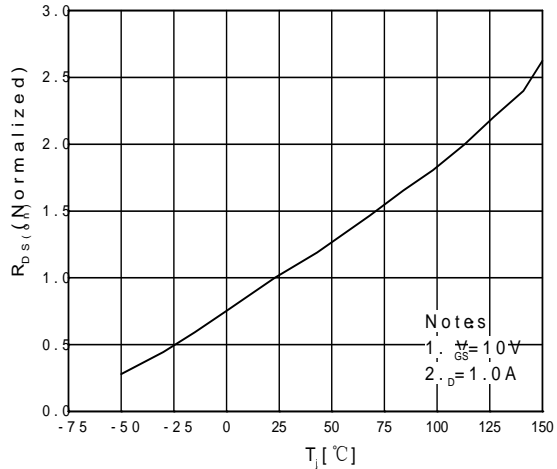


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

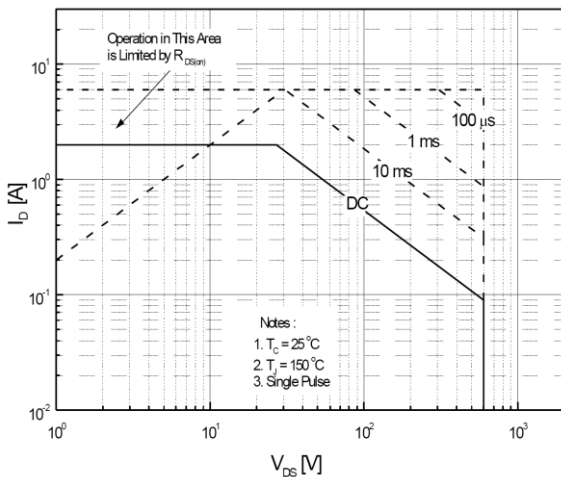
Breakdown Voltage Variation vs. Temperature



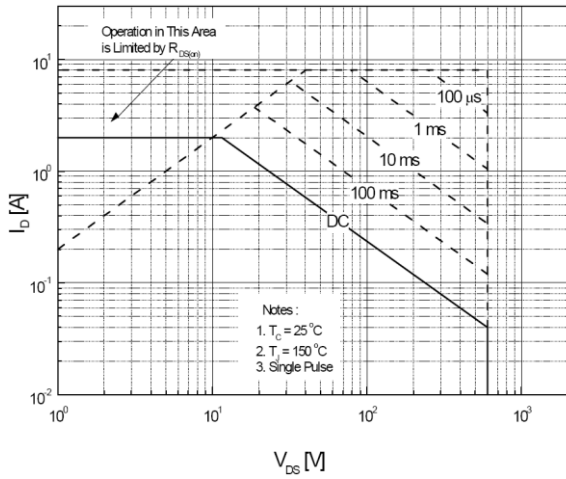
On-Resistance Variation vs. Temperature



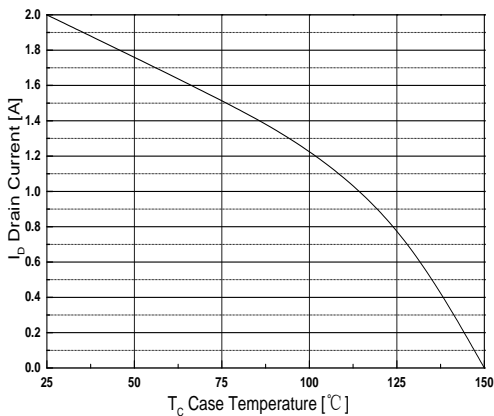
Maximum Safe Operating Area For JCS2N60V/R/C



Maximum Safe Operating Area For JCS2N60F



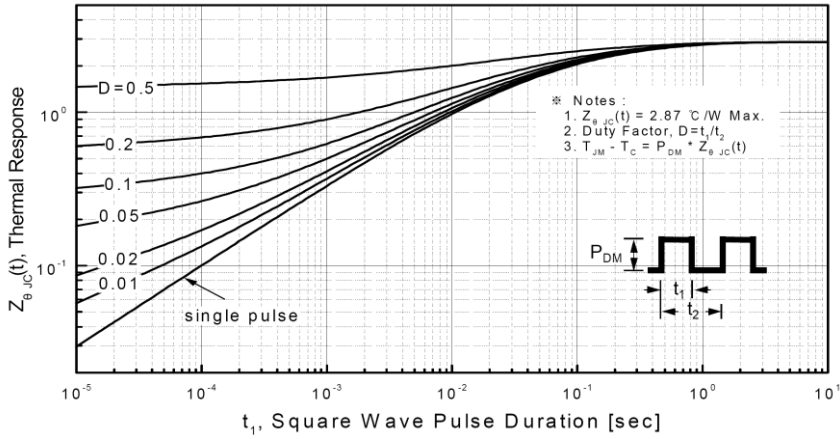
Maximum Drain Current vs. Case Temperature



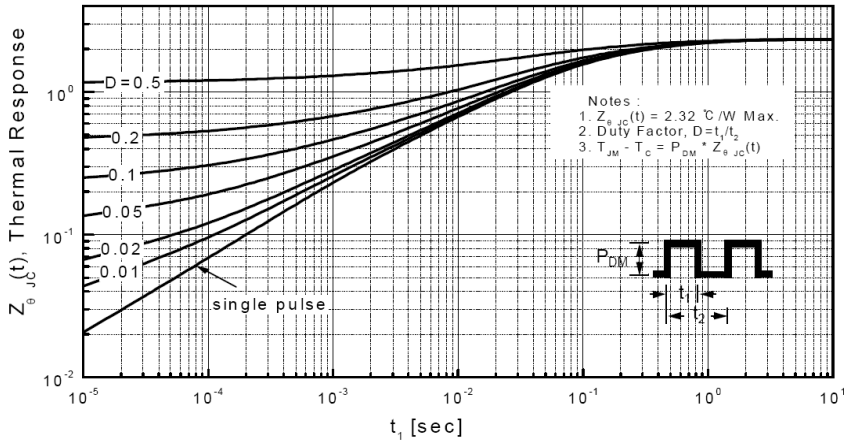


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

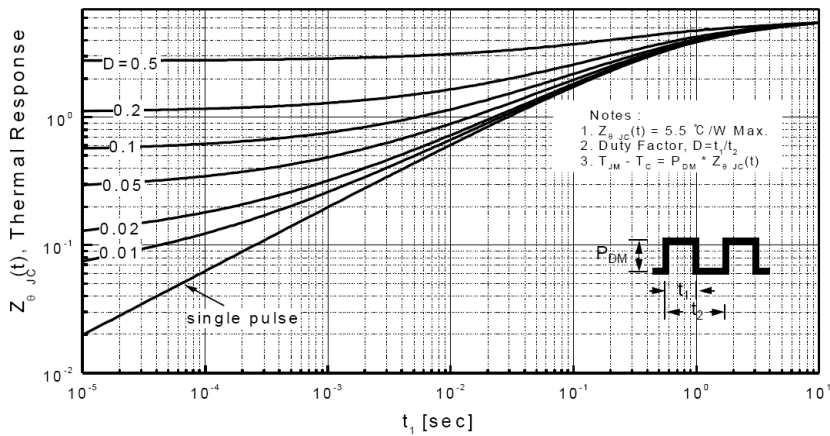
Transient Thermal Response Curve For JCS2N60V/R



Transient Thermal Response Curve For JCS2N60C



Transient Thermal Response Curve For JCS2N60F

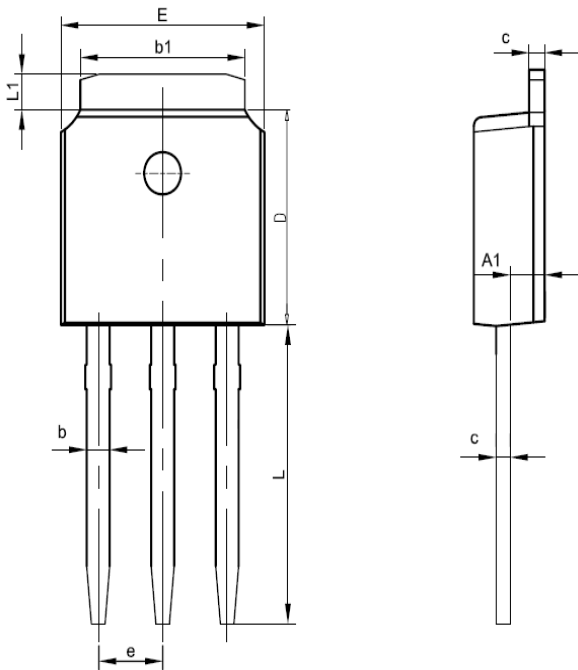




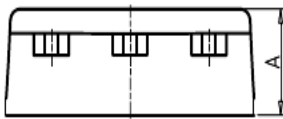
## 外形尺寸 PACKAGE MECHANICAL DATA

IPAK

单位 Unit: mm



SYMBOL	MM	
	MIN	MAX
A	2.1	2.5
A1	0.87	1.27
b	0.63	0.93
b1	5.13	5.53
c	0.40	0.60
D	5.80	6.40
E	6.30	6.90
L	9.10	9.70
e	2.286BSC	
L1	0.82	1.22



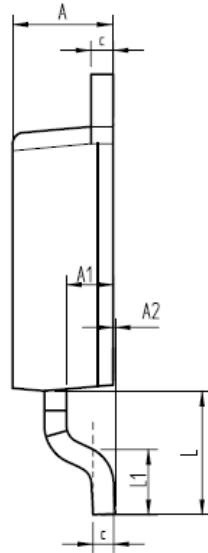
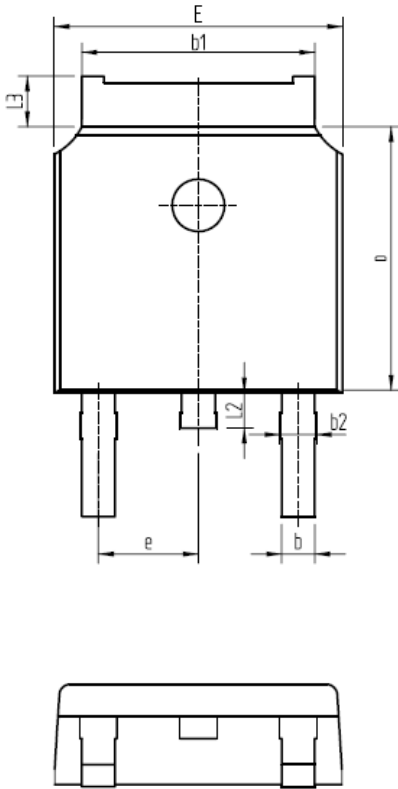




外形尺寸 PACKAGE MECHANICAL DATA

DPAK

单位 Unit: mm



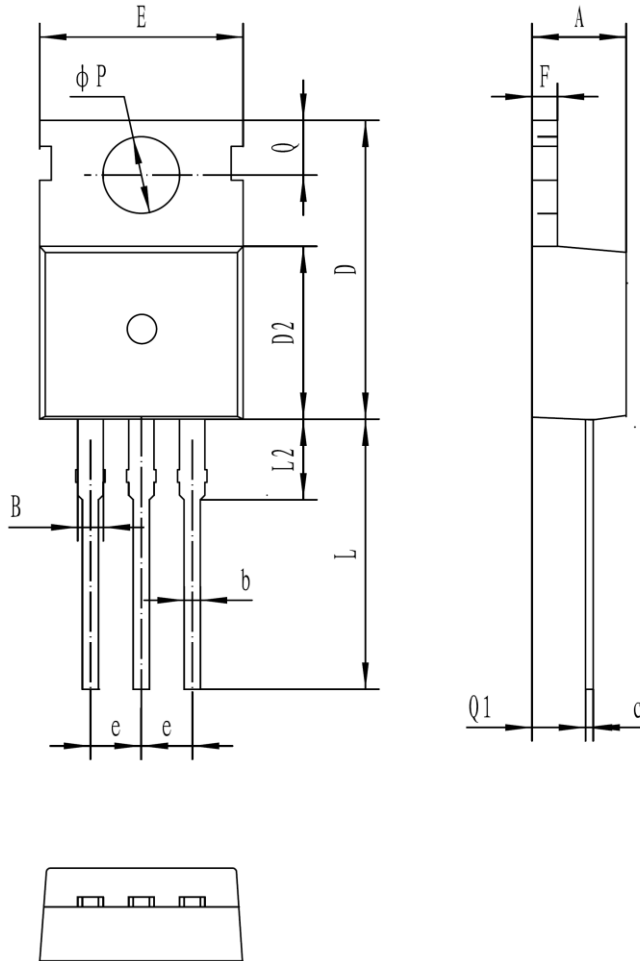
SYMBOL	mm	
	MIN	MAX
A	2.16	2.41
A1	0.97	1.17
A2	0.00	0.15
b	0.63	0.93
b1	5.13	5.53
b2	0.66	0.96
c	0.40	0.60
D	5.80	6.40
E	6.30	6.90
e	2.286BSC	
L	2.50	3.30
L1	1.20	1.80
L2	0.60	1.00
L3	0.85	1.30





TO-220C

单位 Unit: mm



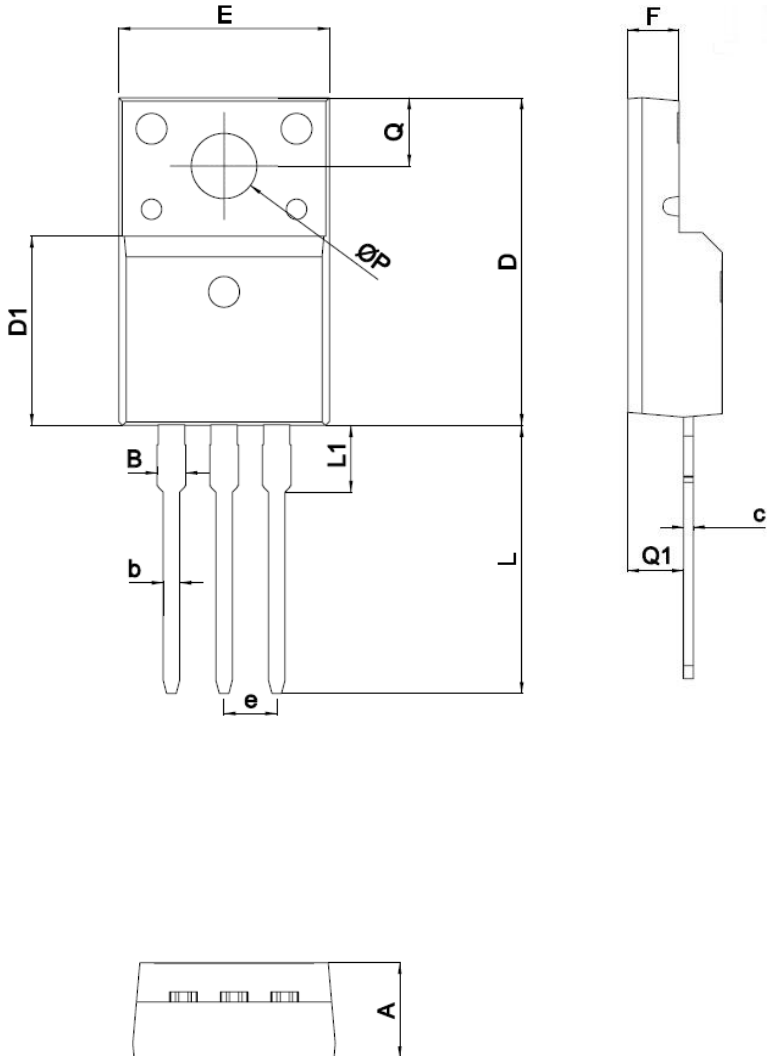
符号 symbol	MIN	MAX
A	4.30	4.70
B	1.10	1.40
b	0.70	0.95
c	0.40	0.65
D	15.20	16.20
D2	9.00	9.40
E	9.70	10.10
e	2.39	2.69
F	1.25	1.40
L	12.60	13.60
L2	2.80	3.20
Q	2.60	3.00
Q1	2.20	2.60
P	3.50	3.80





TO-220MF

单位 Unit: mm



SYMBOL	mm	
	MIN	MAX
A	4.5	4.9
B		1.47
b	0.7	0.9
c	0.45	0.60
D	15.67	16.07
D1	9.04	9.20
e	2.54TYPE	
E	9.96	10.36
F	2.34	2.74
L	12.58	13.38
L1	3.13	3.33
Q	3.2	3.4
Q1	2.56	2.96
ΦP	3.08	3.28



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